

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	((257/700 257/698 257/690 257/100 257/99 257/98 257/93 257/92 257/88 257/84 257/81).CCLS.) and (ingan gainn gan) and "in.sub.xga.sub.1-xn"	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 21:00

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	14523	light adj emitting adj device	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 20:50
2	BRS	L4	390	1 and (ingan gainn gan)	USPAT; US-PGPU B	2001/10/26 20:57
3	BRS	L5	297	4 and sapphire	USPAT; US-PGPU B	2001/10/26 20:57
4	BRS	L6	40	5 and @ay<1996	USPAT; US-PGPU B	2001/10/26 20:58
5	BRS	L7	0	6 and ("in.sub.xga.sub.1-xn")	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 20:58
6	BRS	L8	6	5 and ("in.sub.xga.sub.1-xn")	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 20:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	14523	light adj emitting adj device	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 20:50
2	BRS	L3	8	1 and ("in.sub.xga.sub.1-xn") ("in.sub.xal.sub.yga.sub.1-x-yn") )	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 20:52
3	BRS	L2	6	1 and ("in.sub.xga.sub.1-xn")	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	2001/10/26 20:52

**Application No. 09/711,908**

LED with controlled Indium contains to control the light emission.

East Search						10/26/01
Search	L No.	Hits	Text Search			Data Bases
BRS	L1	11	in.sub.xga.sub.1-xn		10/26/01 15:09	USPAT; EPO; JPO; Derwent; IBM TDB

Search Result						
USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
US 20010034116 A1		16	Semiconductor device with schottky contact and method for forming the same			Lee, Suk Hun , Lee, Yong Hyun , et al.
US 20010030318 A1		34	Nitride semiconductor light-emitting device			Nakamura, Shuji , Nagahama, Shinichi , et al.
US 20010030317 A1		18	Nitride semiconductor light emitting device			Lee, Sung-nam , Park, Yong-jo , et al.
US 20010030316 A1		35	Nitride based semiconductor device and method of forming the same			Kuramoto, Masaru , Yamaguchi, Atsushi
US 20010026950 A1		13	Method of manufacturing a nitrogen-based semiconductor substrate and a semiconductor element by using the same			Sunakawa, Haruo , Usui, Akira
US 20010022495 A1		32	LED lamps			Salam, Hassan P. A.
US 20010012679 A1		11	Method of activating compound semiconductor layer to p-type compound semiconductor layer			Shin, Hyun-Eoi
US 20010009134 A1		5	GaN system compound semiconductor and method for growing crystal thereof			Kim, Chin Kyo , Yoo, Tae Kyung
US 20010005023 A1		25	Method for growing nitride semiconductor crystals, nitride semiconductor device, and method for fabricating the same			Itoh, Kunio , Ishida, Masahiro
US 20010002048 A1		26	Light-emitting device using group III nitride group compound semiconductor			Koike, Masayoshi , Yamakazi, Shiro , et al.
US 20010000916 A1		12	Semiconductor photonic device, method for making the same, and method for forming ZnO film			Kadota, Michio